Designer's™ Data Sheet

Insulated Gate Bipolar Transistor

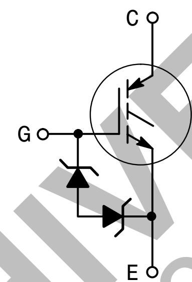
N–Channel Enhancement–Mode Silicon Gate

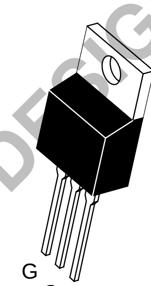
MGP20N60U

IGBT IN TO–220
20 A @ 90°C
31 A @ 25°C
600 VOLTS
VERY LOW
ON–VOLTAGE

This Insulated Gate Bipolar Transistor (IGBT) uses an advanced termination scheme to provide an enhanced and reliable high voltage–blocking capability. It also provides low on–voltage which results in efficient operation at high current.

- Industry Standard TO–220 Package
- High Speed E_{off}: 63 μJ/A typical at 125°C
- Low On–Voltage – 1.7 V typical at 10 A, 125°C
- Robust High Voltage Termination
- ESD Protection Gate–Emitter Zener Diodes





CASE 221A–09
STYLE 9
TO–220AB

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	600	Vdc
Collector–Gate Voltage (R_{GE} = 1.0 MΩ)	V_{CGR}	600	Vdc
Gate–Emitter Voltage — Continuous	V_{GE}	±20	Vdc
Collector Current — Continuous @ T_C = 25°C — Continuous @ T_C = 90°C — Repetitive Pulsed Current (1)	I_{C25} I_{C90} I_{CM}	31 20 62	Adc Apk
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	112 0.89	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to 150	°C
Thermal Resistance — Junction to Case – IGBT — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	1.12 65	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8″ from case for 5 seconds	T_L	260	°C
Mounting Torque, 6–32 or M3 screw	10 lbf•in (1.13 N•m)		

(1) Pulse width is limited by maximum junction temperature. Repetitive rating.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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REV 2

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–to–Emitter Breakdown Voltage (V_{GE} = 0 Vdc, I_C = 25 µAdc)	$V_{(BR)CES}$	600	—	—	Vdc
Temperature Coefficient (Positive)		—	870	—	mV/°C
Emitter–to–Collector Breakdown Voltage (V_{GE} = 0 Vdc, I_{EC} = 100 mAdc)	$V_{(BR)ECS}$	15	—	—	Vdc
Zero Gate Voltage Collector Current (V_{CE} = 600 Vdc, V_{GE} = 0 Vdc)	I_{CES}	—	—	10	µAdc
(V_{CE} = 600 Vdc, V_{GE} = 0 Vdc, T_J = 125°C)		—	—	200	
Gate–Body Leakage Current (V_{GE} = ± 20 Vdc, V_{CE} = 0 Vdc)	I_{GES}	—	—	50	µAdc
ON CHARACTERISTICS (1)					
Collector–to–Emitter On–State Voltage (V_{GE} = 15 Vdc, I_C = 5.0 Adc)	$V_{CE(on)}$	—	1.4	1.7	Vdc
(V_{GE} = 15 Vdc, I_C = 5.0 Adc, T_J = 125°C)		—	1.3	—	
(V_{GE} = 15 Vdc, I_C = 10 Adc)		—	1.7	2.0	
Gate Threshold Voltage (V_{CE} = V_{GE}, I_C = 1.0 mAdc)	$V_{GE(th)}$	3.0	5.0	7.0	Vdc
Threshold Temperature Coefficient (Negative)		—	10	—	mV/°C
Forward Transconductance (V_{CE} = 10 Vdc, I_C = 10 Adc)	g_{fe}	—	7.0	—	Mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance (V_{CE} = 25 Vdc, V_{GE} = 0 Vdc, f = 1.0 MHz)	C_{ies}	—	1060	—	pF
Output Capacitance	C_{oes}	—	99	—	
Transfer Capacitance	C_{res}	—	15	—	
SWITCHING CHARACTERISTICS (1)					
Turn–On Delay Time (V_{CC} = 360 Vdc, I_C = 10 Adc, V_{GE} = 15 Vdc, L = 300 µH, R_G = 20 Ω) Energy losses include “tail”	$t_{d(on)}$	—	43	—	ns
Rise Time	t_r	—	45	—	
Turn–Off Delay Time	$t_{d(off)}$	—	144	—	
Fall Time	t_f	—	175	—	
Turn–Off Switching Loss	E_{off}	—	340	—	µJ
Turn–On Delay Time (V_{CC} = 360 Vdc, I_C = 10 Adc, V_{GE} = 15 Vdc, L = 300 µH, R_G = 20 Ω, T_J = 125°C) Energy losses include “tail”	$t_{d(on)}$	—	43	—	ns
Rise Time	t_r	—	56	—	
Turn–Off Delay Time	$t_{d(off)}$	—	235	—	
Fall Time	t_f	—	220	—	
Turn–Off Switching Loss	E_{off}	—	625	—	µJ
Gate Charge (V_{CC} = 360 Vdc, I_C = 10 Adc, V_{GE} = 15 Vdc)	Q_T	—	57	—	nC
	Q_1	—	12	—	
	Q_2	—	25	—	
INTERNAL PACKAGE INDUCTANCE					
Internal Emitter Inductance (Measured from the emitter lead 0.25″ from package to emitter bond pad)	L_E	—	7.5	—	nH

(1) Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.

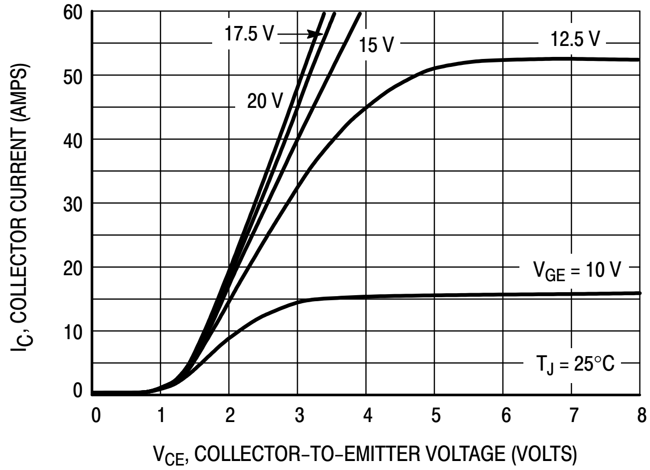


Figure 1. Output Characteristics

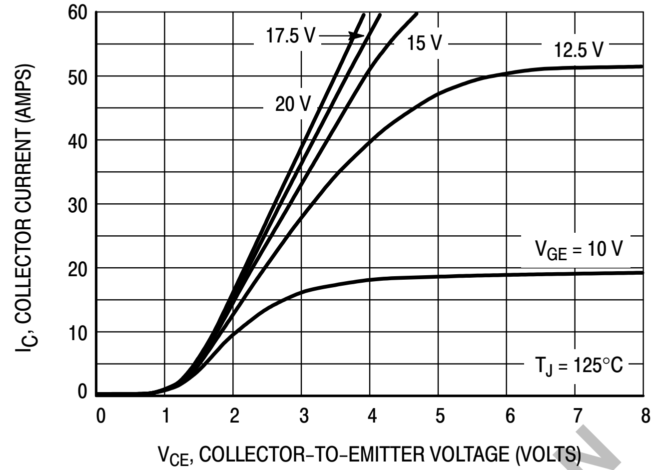


Figure 2. Output Characteristics

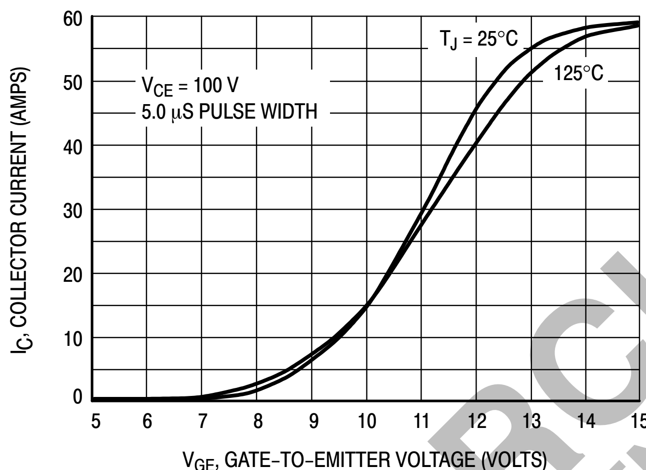


Figure 3. Transfer Characteristics

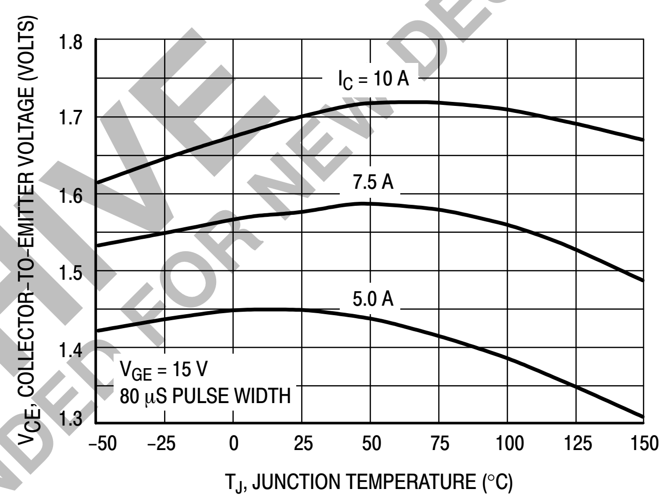


Figure 4. Collector–To–Emitter Saturation Voltage versus Junction Temperature

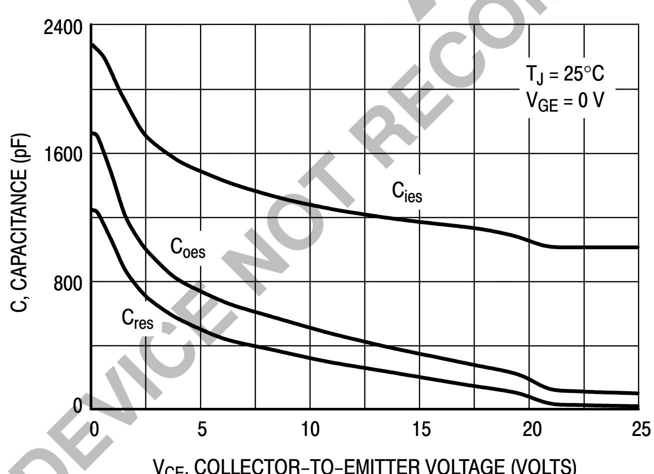


Figure 5. Capacitance Variation

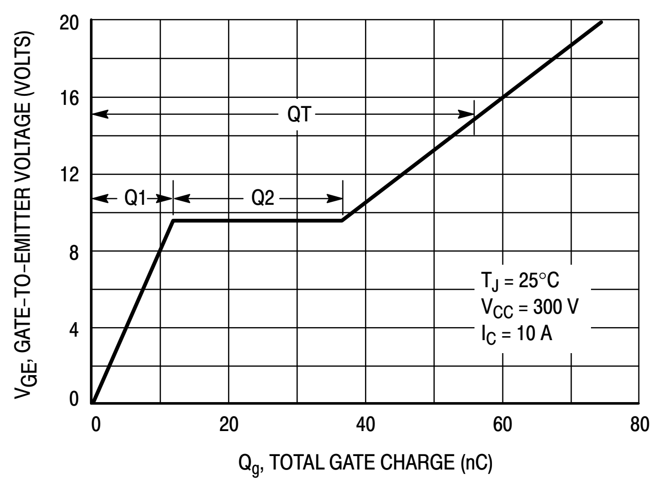


Figure 6. Gate–To–Emitter Voltage versus Total Charge

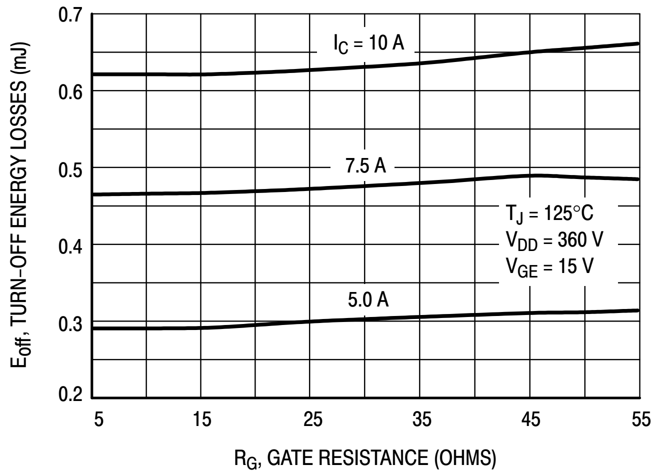


Figure 7. Turn–Off Energy Losses versus Gate Resistance

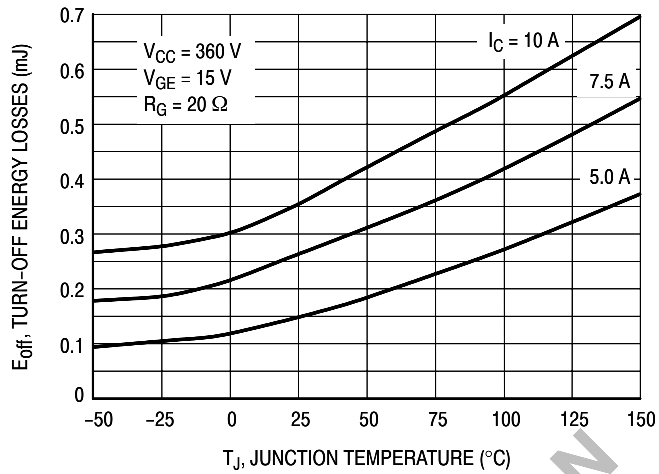


Figure 8. Turn–Off Energy Losses versus Junction Temperature

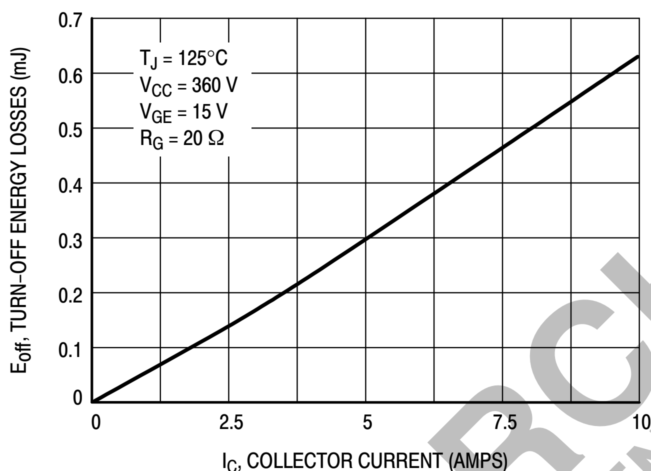


Figure 9. Turn–Off Energy Losses versus Collector Current

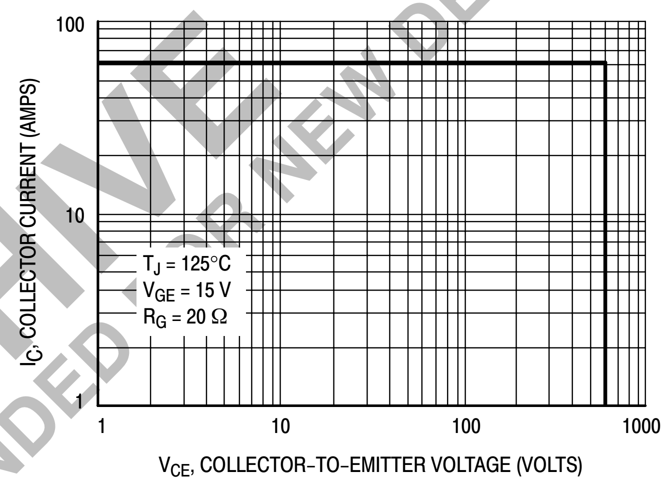
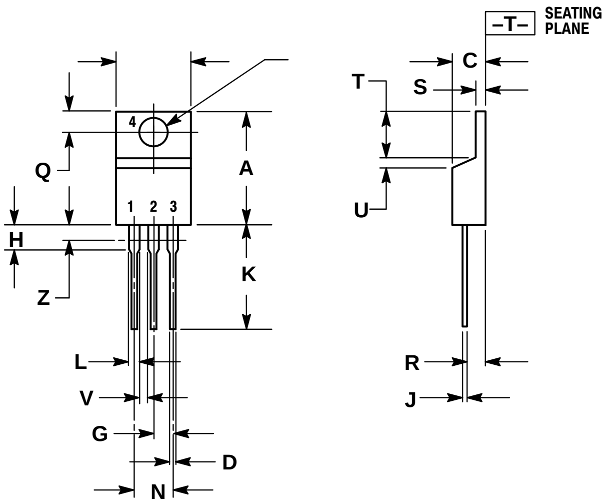


Figure 10. Reverse Biased Safe Operating Area

PACKAGE DIMENSIONS



STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

CASE 221A–09
ISSUE Z

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